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A SPLIT-GATE FLASH WITH SOURCE/DRAIN MULTI-SHARING

SUGGESTED TITLE: MULTI-BIT SPLIT-GATE (MSG) FLASH CELL WITH
MULTI-SHARED SOURCE/DRAIN

This application is related to application docket TSMC01-282, "A Flash EEPROM with Function of Single Bit Erasing by an Application of Negative Control Gate Selection," Serial No: 10/043726, and Filing Date: Jan. 10 2002; and to application docket TSMC01-280, "A Flash EEPROM with Function Bit by Bit Erasing," Serial No: 10/686794, and Filing Date: Oct. 16, 2003.

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BACKGROUND OF THE INVENTION

(1) Field of the Invention

The present invention relates to the manufacture of semiconductor devices, and in particular, to split-gate flash memory cells and to a method of forming high density flash memory arrays using the same.

(2) Description of the Related Art